

Figure 1. AFM images and cross-sectional height profile of etch pits observed on the (100) and (001) β -Ga₂O₃ surface. Etch pit on the (a) (100) plane with a width of $\sim 1 \mu\text{m}$ and a depth of $\sim 34 \text{ nm}$ and (b) (001) plane with a width of $\sim 10 \mu\text{m}$ and a depth of $\sim 200 \text{ nm}$.

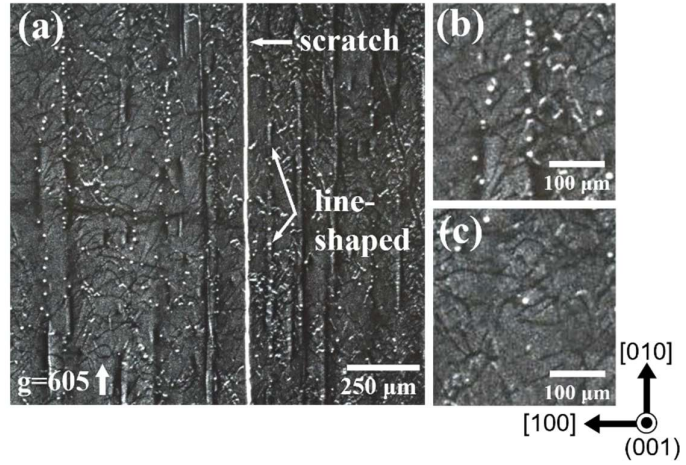


Figure 2. (a) X-ray topography image of (a) the (001)-oriented Ga₂O₃ crystal with $g=605$, where defects related to (b) dots and (c) curved lines.